Abstracts

A Silicon MOS Process for Integrated RF Power Amplifiers (1996 [MCS])

C. Dragon, J. Costa, D. Lamey, D. Ngo, W. Burger and N. Camilleri. "A Silicon MOS Process for Integrated RF Power Amplifiers (1996 [MCS])." 1996 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 98. (1996 [MCS]): 189-192.

A silicon-based technology is presented which integrates passive components with a silicon Power MOSFET for use in Integrated Power Amplifiers at UHF, VHF, and RF frequencies. This low-cost process incorporates capacitors, inductors, resistors, ground vias, transmission lines, and an ESD protection diode. A design library containing models and layouts for the active and passive components was compiled.

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